ECE 310- Lecture 14.

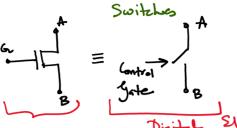
Wednesday, February 14, 2018

10:32 AM

Chapter 6:

Mos Transisters Basics

atterminal



Jigital Sheetronius

MOSFET

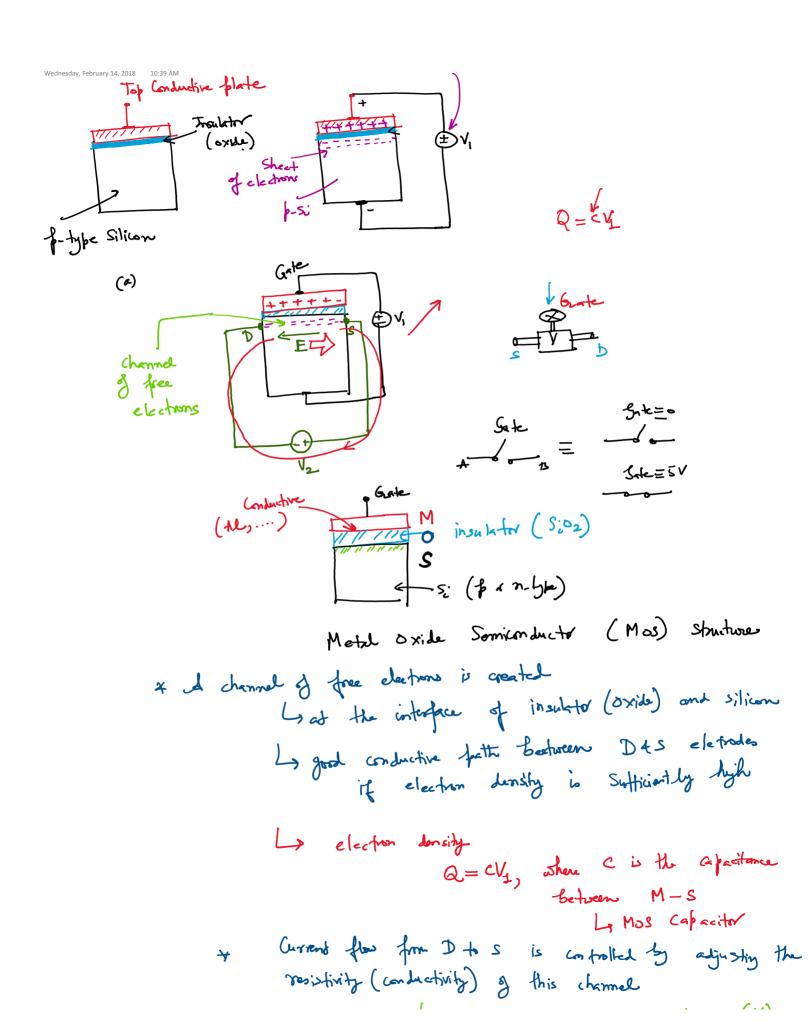
3 Metal Oxide Semiconductor

La Fich Effect

Analog Steethomic

Controlled Sources La Amplifiers Li Hers

New Section 1 Page 1



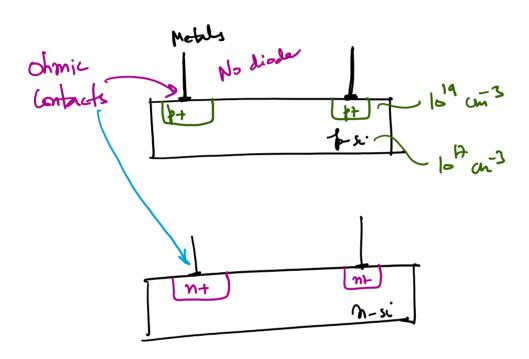
resistivity (conductivity) of this channel

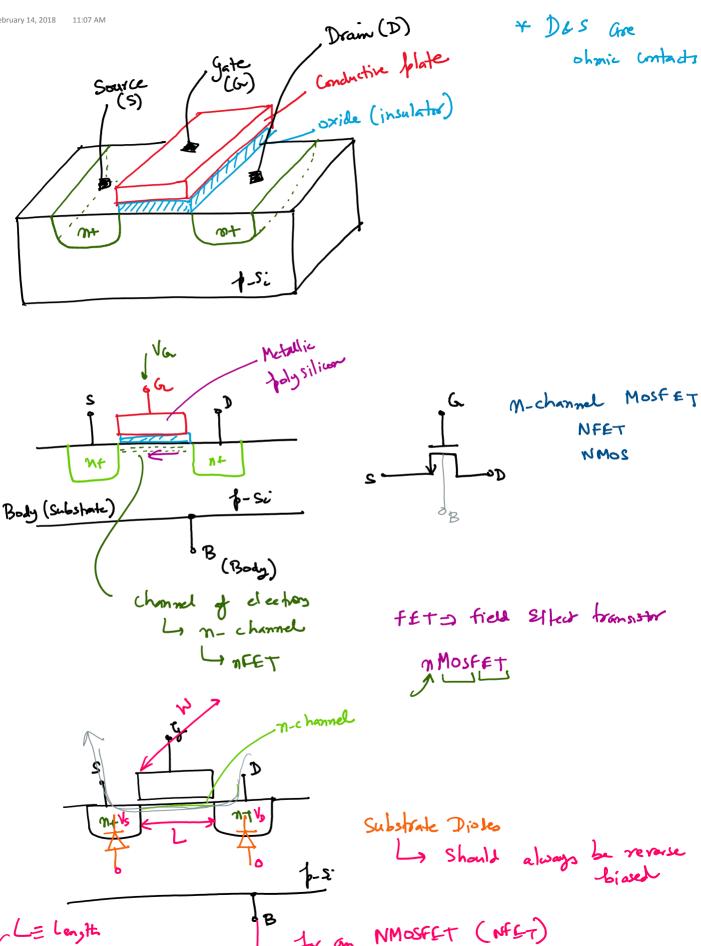
Ly controlled by the gate in type (V)

24 J

ECE 445 VLSI DESIGN Spring 2019

ps





L= Length

W= with

L= 14 mm

L= 14 mm